



**THE DATASHEET OF  
MRFE6S9135HSR3**



# RF Power Field Effect Transistors

## N-Channel Enhancement-Mode Lateral MOSFETs

Designed for broadband commercial and industrial applications with frequencies up to 1000 MHz. The high gain and broadband performance of these devices make them ideal for large-signal, common-source amplifier applications in 28 volt base station equipment.

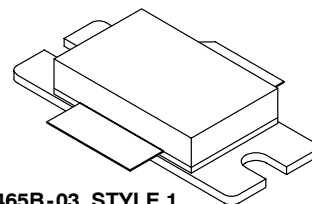
- Typical Single-Carrier W-CDMA Performance:  $V_{DD} = 28$  Volts,  $I_{DQ} = 1000$  mA,  $P_{out} = 39$  Watts Avg., Full Frequency Band, 3GPP Test Model 1, 64 DPCH with 50% Clipping, Channel Bandwidth = 3.84 MHz, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF.  
 Power Gain — 21 dB  
 Drain Efficiency — 32.3%  
 Device Output Signal PAR — 6.4 dB @ 0.01% Probability on CCDF  
 ACPR @ 5 MHz Offset — -39.5 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 32 Vdc, 940 MHz,  $P_{out} = 180$  W CW (3 dB Input Overdrive from Rated  $P_{out}$ ), Designed for Enhanced Ruggedness

### Features

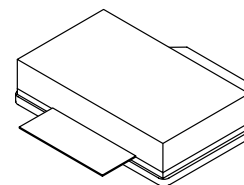
- 100% PAR Tested for Guaranteed Output Power Capability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32  $V_{DD}$  Operation
- Integrated ESD Protection
- Optimized for Doherty Applications
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

**MRFE6S9135HR3**  
**MRFE6S9135HSR3**

**940 MHz, 39 W AVG., 28 V**  
**SINGLE W-CDMA**  
**LATERAL N-CHANNEL**  
**RF POWER MOSFETs**



**CASE 465B-03, STYLE 1**  
**NI-880**  
**MRFE6S9135HR3**



**CASE 465C-02, STYLE 1**  
**NI-880S**  
**MRFE6S9135HSR3**

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-0.5, +66	Vdc
Gate-Source Voltage	$V_{GS}$	-0.5, +12	Vdc
Storage Temperature Range	$T_{stg}$	- 65 to +150	°C
Case Operating Temperature	$T_C$	150	°C
Operating Junction Temperature (1,2)	$T_J$	225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		°C/W
Case Temperature 80°C, 136 W CW		0.39	
Case Temperature 80°C, 39 W CW		0.48	

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22-A114)	II (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

**Table 4. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Off Characteristics</b>					
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 66\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	10	$\mu\text{Adc}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	1	$\mu\text{Adc}$
Gate-Source Leakage Current ( $V_{GS} = 5\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	—	—	10	$\mu\text{Adc}$

**On Characteristics**

Gate Threshold Voltage ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 400\ \mu\text{Adc}$ )	$V_{GS(th)}$	1.4	2.1	2.9	Vdc
Gate Quiescent Voltage ( $V_{DD} = 28\text{ Vdc}$ , $I_D = 1000\ \text{mAdc}$ , Measured in Functional Test)	$V_{GS(Q)}$	2.2	2.9	3.7	Vdc
Drain-Source On-Voltage ( $V_{GS} = 10\text{ Vdc}$ , $I_D = 2.8\ \text{Adc}$ )	$V_{DS(on)}$	0.15	0.2	0.35	Vdc

**Dynamic Characteristics** <sup>(1)</sup>

Reverse Transfer Capacitance ( $V_{DS} = 28\text{ Vdc} \pm 30\ \text{mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{rss}$	—	1.3	—	pF
Output Capacitance ( $V_{DS} = 28\text{ Vdc} \pm 30\ \text{mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{oss}$	—	410	—	pF
Input Capacitance ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc} \pm 30\ \text{mV(rms)ac}$ @ 1 MHz)	$C_{iss}$	—	343	—	pF

**Functional Tests** (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 1000\ \text{mA}$ ,  $P_{out} = 39\ \text{W Avg. W-CDMA}$ ,  $f = 940\ \text{MHz}$ , Single-Carrier W-CDMA, 3.84 MHz Channel Bandwidth Carrier. ACPR measured in 3.84 MHz Channel Bandwidth @  $\pm 5\ \text{MHz}$  Offset. PAR = 7.5 dB @ 0.01% Probability on CCDF.

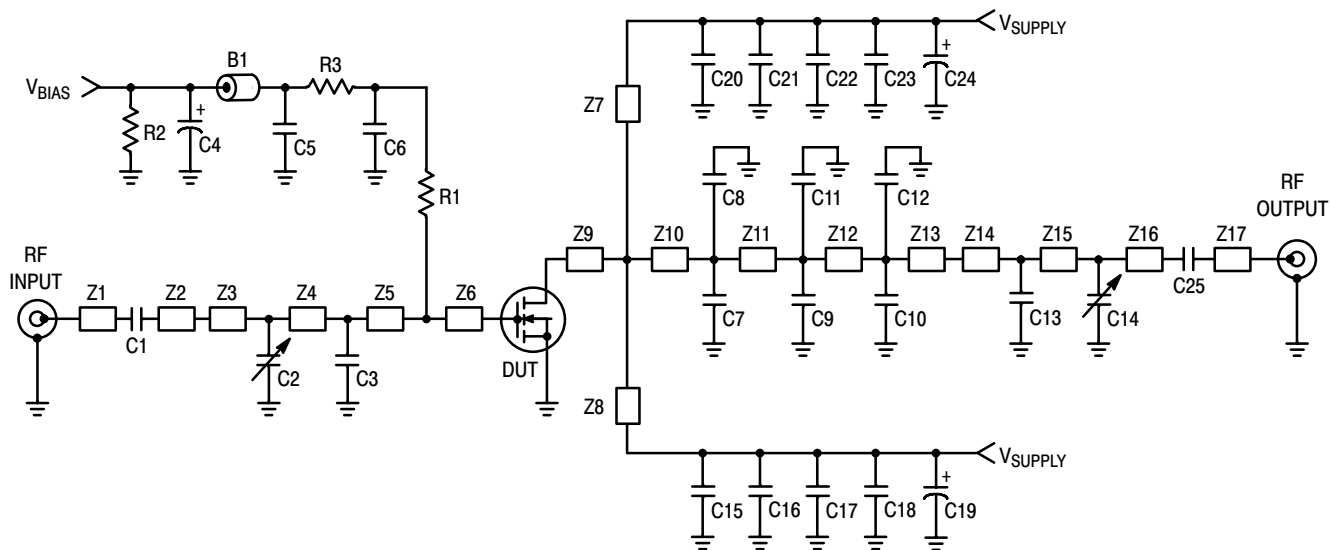
Power Gain	$G_{ps}$	20	21	23	dB
Drain Efficiency	$\eta_D$	30.5	32.3	—	%
Output Peak-to-Average Ratio @ 0.01% Probability on CCDF	PAR	6.1	6.4	—	dB
Adjacent Channel Power Ratio	ACPR	—	-39.5	-38	dBc
Input Return Loss	IRL	—	-15	-9	dB

1. Part internally matched both on input and output.

(continued)

**Table 4. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Typical Performances</b> (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$ , $I_{DQ} = 1000\text{ mA}$ , 920-960 MHz Bandwidth					
Video Bandwidth @ 160 W PEP $P_{out}$ where $IM3 = -30\text{ dBc}$ (Tone Spacing from 100 kHz to VBW) $\Delta IMD3 = IMD3 @ \text{VBW frequency} - IMD3 @ 100\text{ kHz} < 1\text{ dBc}$ (both sidebands)	VBW	—	10	—	MHz
Gain Flatness in 40 MHz Bandwidth @ $P_{out} = 39\text{ W Avg.}$	$G_F$	—	0.3	—	dB
Average Deviation from Linear Phase in 40 MHz Bandwidth @ $P_{out} = 135\text{ W CW}$	$\Phi$	—	1	—	$^\circ$
Average Group Delay @ $P_{out} = 135\text{ W CW}$ , $f = 940\text{ MHz}$	Delay	—	3.6	—	ns
Part-to-Part Insertion Phase Variation @ $P_{out} = 135\text{ W CW}$ , $f = 940\text{ MHz}$ , Six Sigma Window	$\Delta\Phi$	—	19	—	$^\circ$
Gain Variation over Temperature ( $-30^\circ\text{C}$ to $+85^\circ\text{C}$ )	$\Delta G$	—	0.015	—	dB/ $^\circ\text{C}$
Output Power Variation over Temperature ( $-30^\circ\text{C}$ to $+85^\circ\text{C}$ )	$\Delta P_{1dB}$	—	0.01	—	dBm/ $^\circ\text{C}$



Z1	0.263" x 0.065" Microstrip	Z11	0.202" x 0.980" x 0.444" Taper
Z2	0.310" x 0.065" Microstrip	Z12	0.114" x 0.444" Microstrip
Z3	0.910" x 0.120" Microstrip	Z13	0.145" x 0.444" x 0.110" Taper
Z4	0.248" x 1.020" x 0.120" Taper	Z14	0.180" x 0.110" Microstrip
Z5	0.363" x 1.020" Microstrip	Z15	0.585" x 0.110" Microstrip
Z6	0.057" x 1.120" Microstrip	Z16	0.443" x 0.065" Microstrip
Z7, Z8	0.823" x 0.120" Microstrip	Z17	0.274" x 0.065" Microstrip
Z9	0.060" x 0.980" Microstrip	PCB	Taconic RF-35, 0.030", $\epsilon_r = 3.5$
Z10	0.149" x 0.980" Microstrip		

**Figure 1. MRFE6S9135HR3(HSR3) Test Circuit Schematic**

**Table 5. MRFE6S9135HR3(HSR3) Test Circuit Component Designations and Values**

Part	Description	Part Number	Manufacturer
B1	Short RF Bead	2743019447	Fair-Rite
C1, C6, C15, C20, C25	39 pF Chip Capacitors	ATC100B390JT500XT	ATC
C2, C14	0.8 - 8.0 pF Variable Capacitors, Gigatrim	27291SL	Johanson
C3	2.0 pF Chip Capacitor	ATC100B2R0JT500XT	ATC
C4	33 $\mu$ F, 25 V Electrolytic Capacitor	EMVY250ADA330MF55G	Nippon Chemi-Con
C5, C16, C17, C18, C21, C22, C23	10 $\mu$ F, 50 V Chip Capacitors	GRM55DR61H106KA88B	Murata
C7, C8	6.8 pF Chip Capacitors	ATC100B6R8JT500XT	ATC
C9, C10, C11, C12, C13	4.7 pF Chip Capacitors	ATC100B4R7JT500XT	ATC
C19, C24	470 $\mu$ F, 63 V Electrolytic Capacitors	EKME630ELL471MK25S	United Chemi-Con
R1, R3	3.3 $\Omega$ , 1/3 W Chip Resistors	CRCW12103R30FKEA	Vishay
R2	2.2 K $\Omega$ , 1/4 W Chip Resistor	CRCW12062201FKEA	Vishay

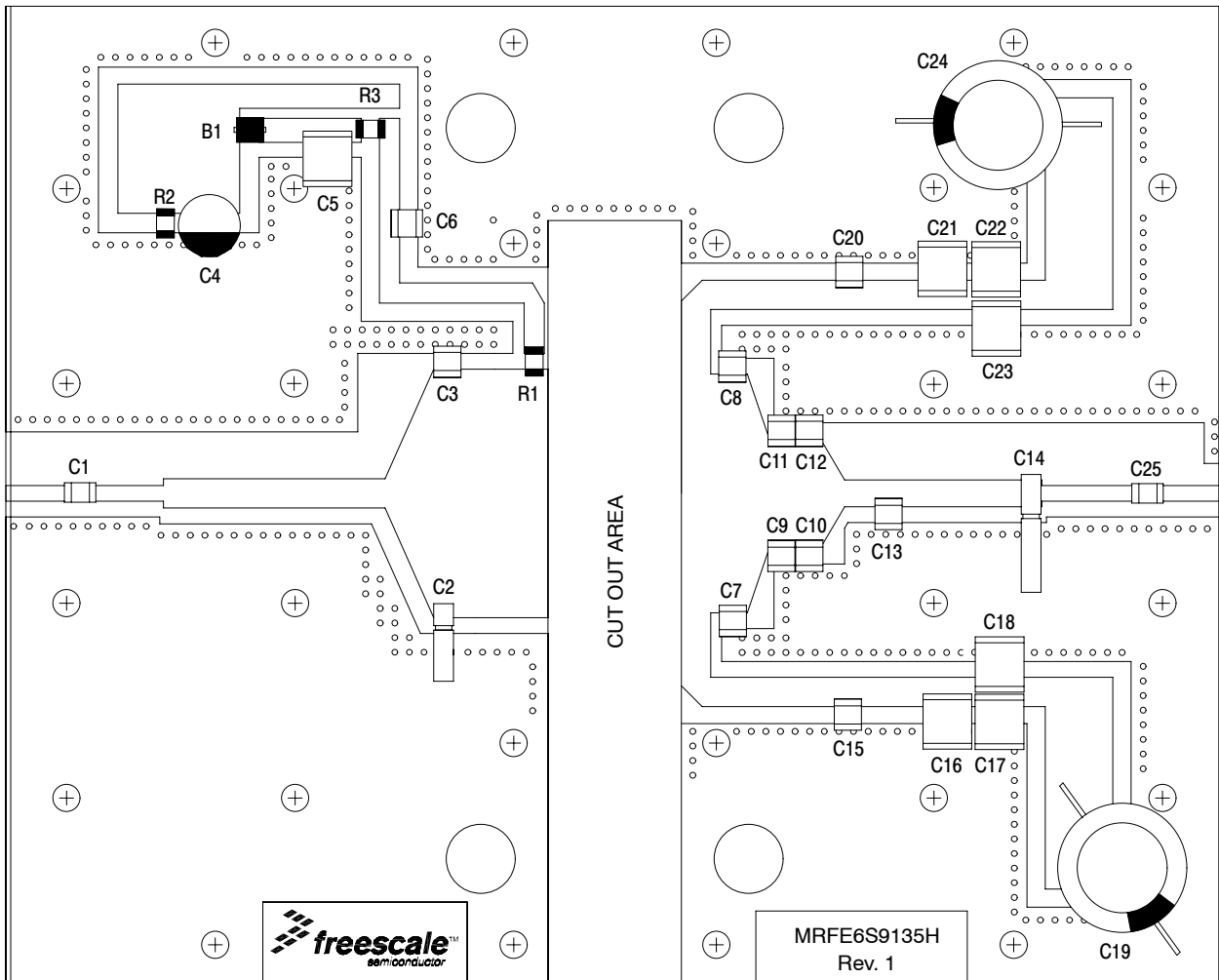
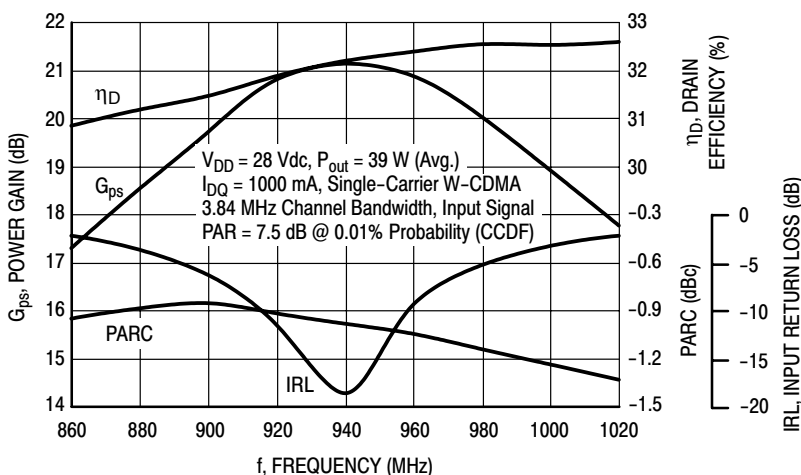
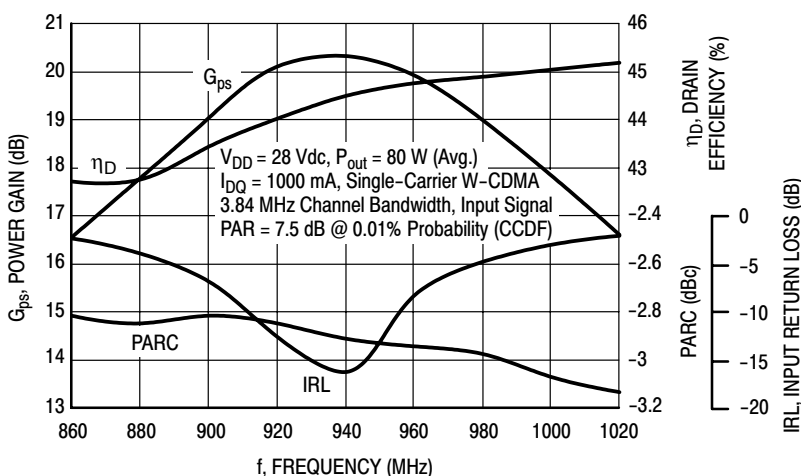


Figure 2. MRFE6S9135HHR3 (HSR3) Test Circuit Component Layout

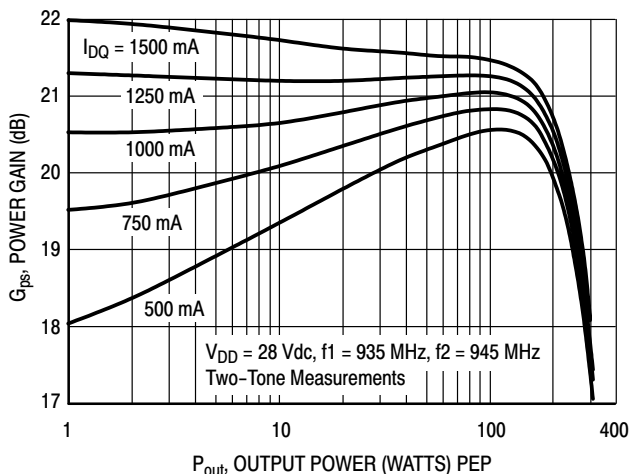
### TYPICAL CHARACTERISTICS



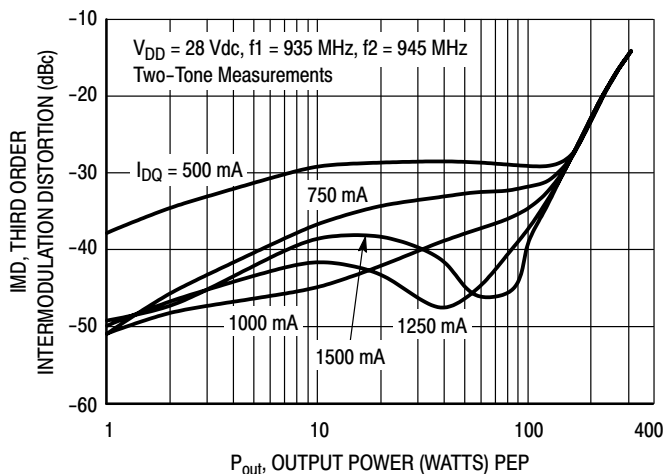
**Figure 3. Single-Carrier W-CDMA Broadband Performance @ P<sub>out</sub> = 39 Watts Avg.**



**Figure 4. Single-Carrier W-CDMA Broadband Performance @ P<sub>out</sub> = 80 Watts Avg.**

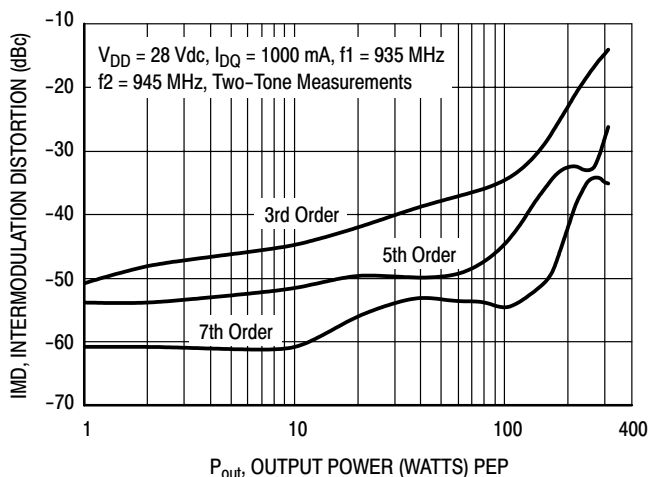


**Figure 5. Two-Tone Power Gain versus Output Power**

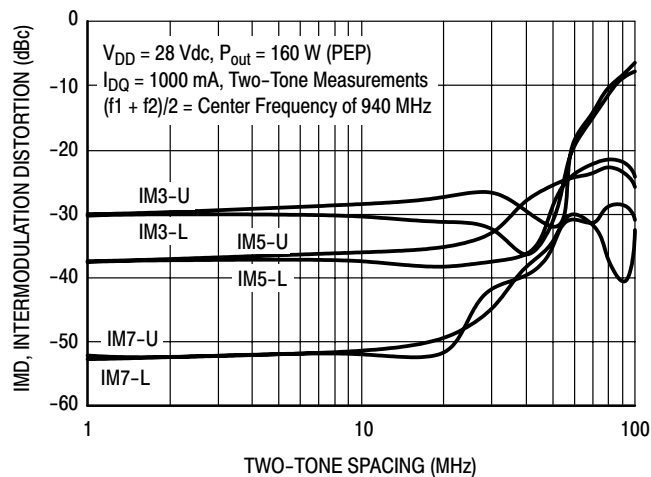


**Figure 6. Third Order Intermodulation Distortion versus Output Power**

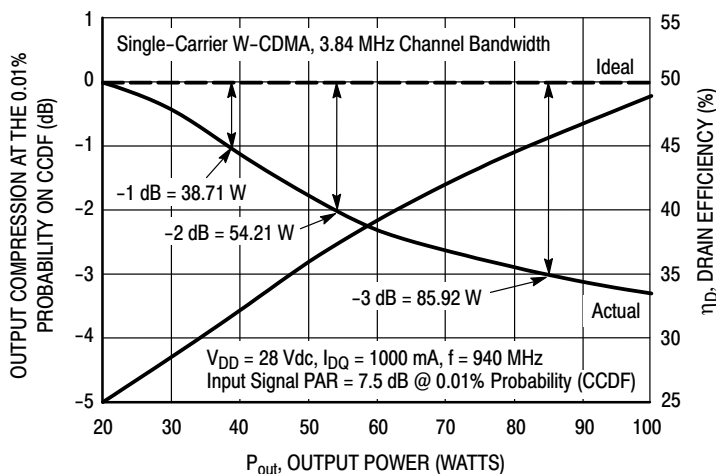
### TYPICAL CHARACTERISTICS



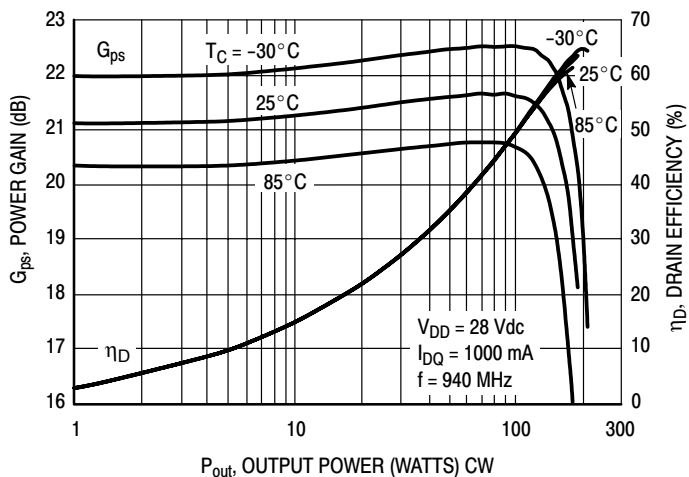
**Figure 7. Intermodulation Distortion Products versus Output Power**



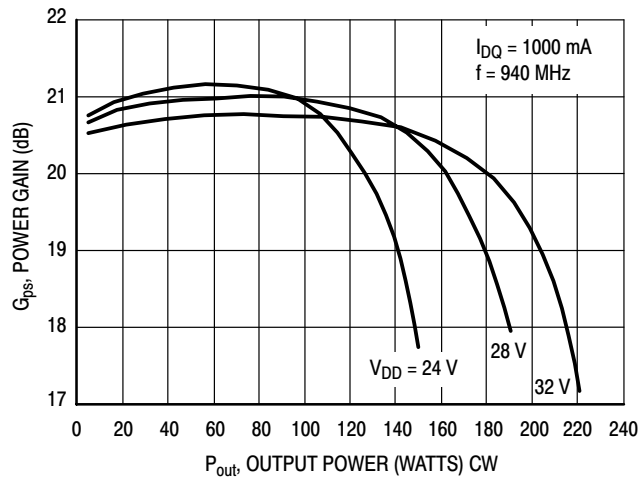
**Figure 8. Intermodulation Distortion Products versus Tone Spacing**



**Figure 9. Output Peak-to-Average Ratio Compression (PARC) versus Output Power**

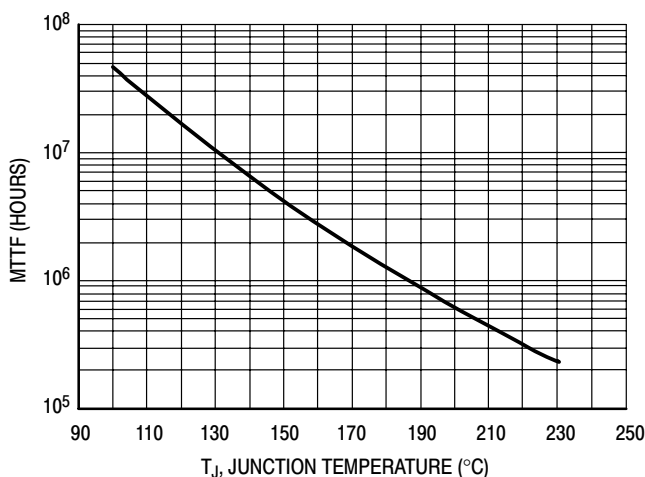


**Figure 10. Power Gain and Drain Efficiency versus CW Output Power**



**Figure 11. Power Gain versus Output Power**

### TYPICAL CHARACTERISTICS

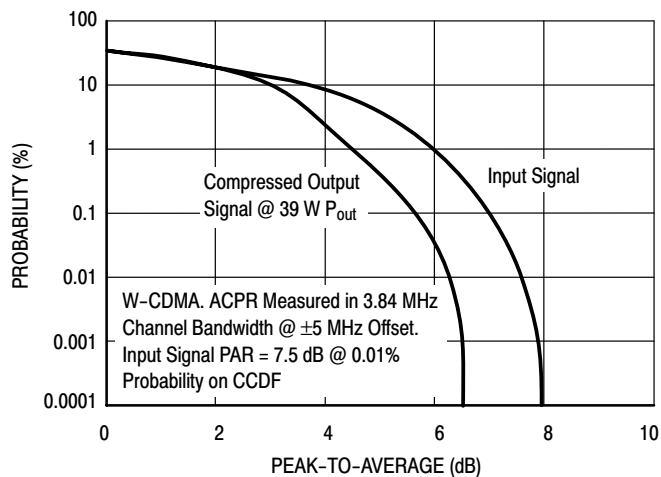


This above graph displays calculated MTTF in hours when the device is operated at  $V_{DD} = 28$  Vdc,  $P_{out} = 39$  W Avg., and  $\eta_D = 32.3\%$ .

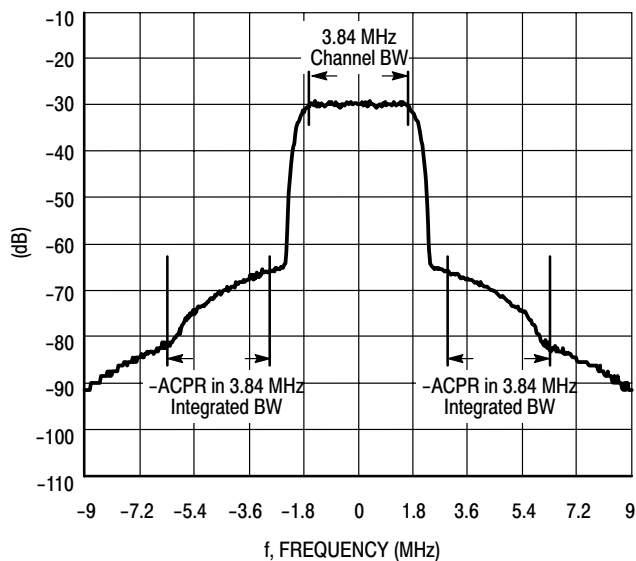
MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

**Figure 12. MTTF versus Junction Temperature**

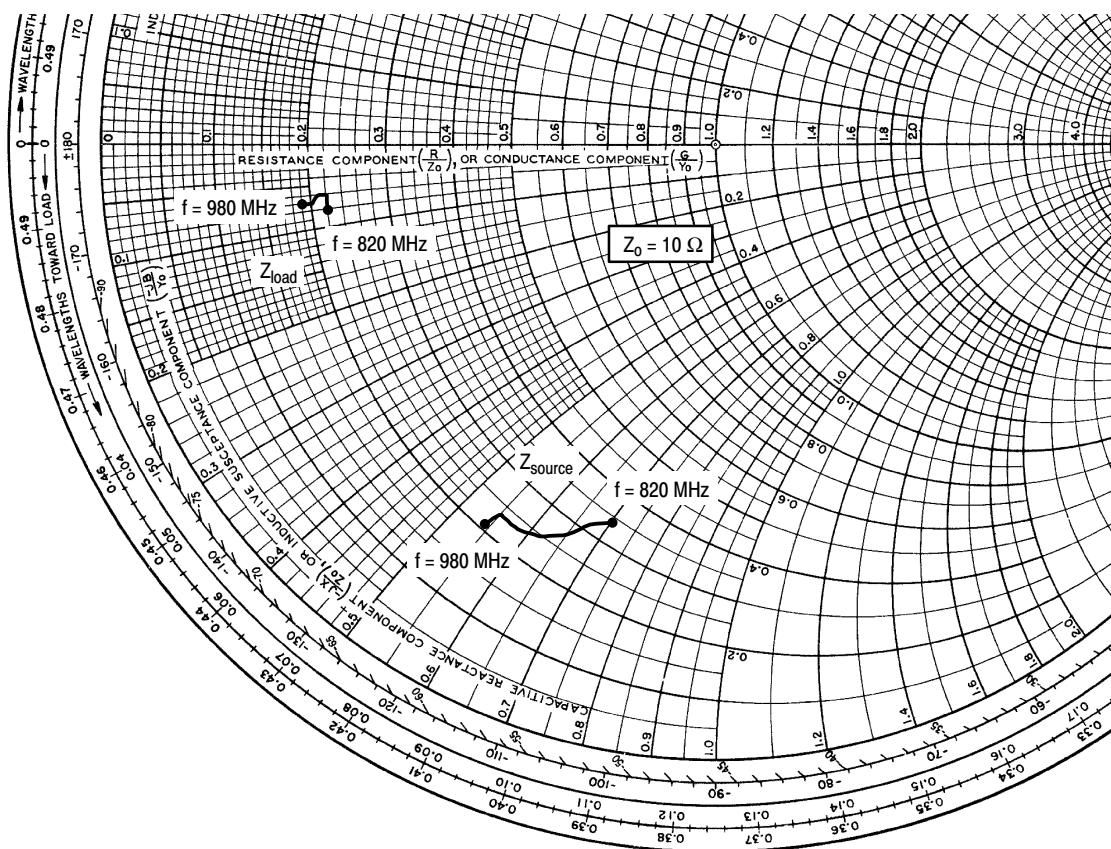
### W-CDMA TEST SIGNAL



**Figure 13. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 50% Clipping, Single-Carrier Test Signal**



**Figure 14. Single-Carrier W-CDMA Spectrum**



$V_{DD} = 28 \text{ Vdc}$ ,  $I_{DQ} = 1000 \text{ mA}$ ,  $P_{out} = 39 \text{ W Avg.}$

f MHz	$Z_{source}$ $\Omega$	$Z_{load}$ $\Omega$
820	3.39 - j6.99	2.18 - j0.80
840	3.32 - j6.86	2.20 - j0.71
860	3.05 - j6.74	2.21 - j0.66
880	2.72 - j6.47	2.20 - j0.64
900	2.46 - j6.16	2.20 - j0.64
920	2.41 - j5.80	2.18 - j0.62
940	2.41 - j5.58	2.13 - j0.63
960	2.38 - j5.45	2.03 - j0.66
980	2.13 - j5.38	1.87 - j0.70

$Z_{source}$  = Test circuit impedance as measured from gate to ground.

$Z_{load}$  = Test circuit impedance as measured from drain to ground.

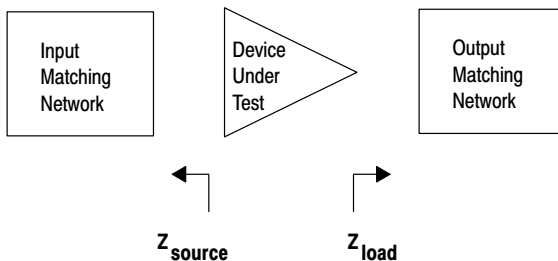
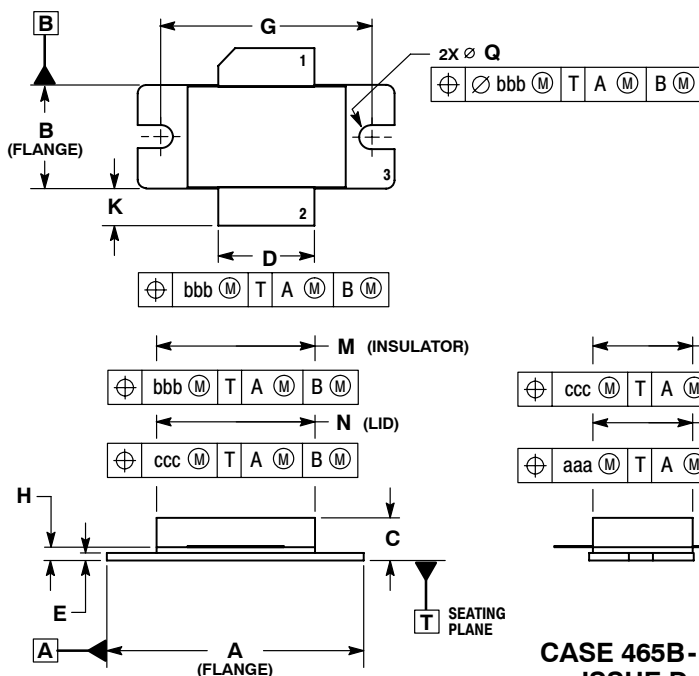


Figure 15. Series Equivalent Source and Load Impedance

### PACKAGE DIMENSIONS

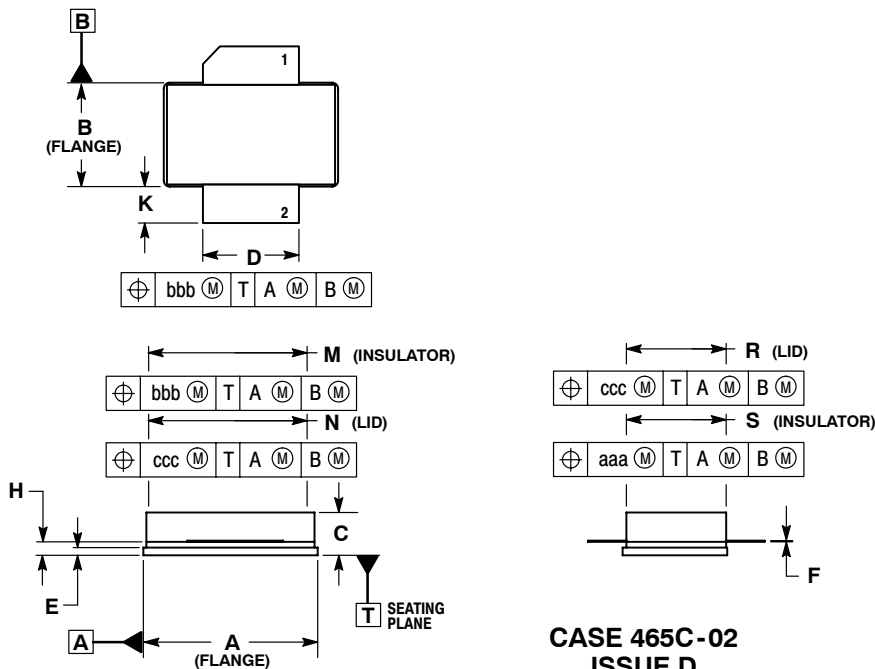


**CASE 465B-03  
ISSUE D  
NI-880  
MRFE6S9135HR3**

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
  4. DELETED

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.535	0.545	13.6	13.8
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
Q	∅ .118	∅ .138	∅ 3.00	∅ 3.51
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007 REF		0.178 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:  
PIN 1. DRAIN  
2. GATE  
3. SOURCE



**CASE 465C-02  
ISSUE D  
NI-880S  
MRFE6S9135HSR3**

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.905	0.915	22.99	23.24
B	0.535	0.545	13.60	13.80
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007 REF		0.178 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:  
PIN 1. DRAIN  
2. GATE  
3. SOURCE

## PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

### Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

### Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

## REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Nov. 2007	<ul style="list-style-type: none"> <li>• Initial Release of Data Sheet</li> </ul>
1	Nov. 2007	<ul style="list-style-type: none"> <li>• Updated Fig. 12, MTTF versus Junction Temperature, to reflect a 32.3% typical efficiency rating, p. 8</li> </ul>

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